

# DMN62D1LFB-7B Datasheet



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DiGi Electronics Part Number	DMN62D1LFB-7B-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	DMN62D1LFB-7B
Description	MOSFET N-CH 60V 320MA 3DFN
Detailed Description	N-Channel 60 V 320mA (Ta) 500mW (Ta) Surface Mount X1-DFN1006-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

DMN62D1LFB-7B

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

1.5V, 4V

Vgs(th) (Max) @ Id:

1V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

X1-DFN1006-3

Base Product Number:

DMN62

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

320mA (Ta)

Rds On (Max) @ Id, Vgs:

20hm @ 100mA, 4V

Gate Charge (Qg) (Max) @ Vgs:

0.9 nC @ 4.5 V

Input Capacitance (Ciss) (Max) @ Vds:

64 pF @ 25 V

Power Dissipation (Max):

500mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

3-UFDNFN

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN62D1LFB

## N-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$ $T_A = +25^\circ\text{C}$
60V	$2\Omega @ V_{GS} = 4V$	407mA
	$2.5\Omega @ V_{GS} = 2.5V$	364mA

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

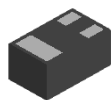
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

## Mechanical Data

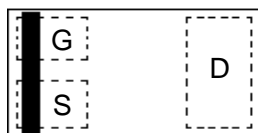
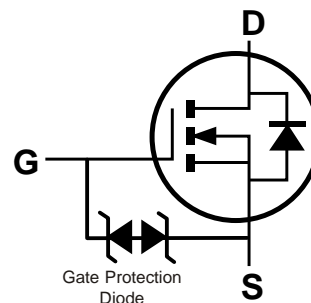
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e4)**
- Weight: 0.001 grams (Approximate)



X1-DFN1006-3



Bottom View

Top View  
Pin-Out

Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMN62D1LFB-7B	NQ	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

DMN62D1LFB-7B	 Top View Bar Denotes Gate and Source Side	NQ = Part Marking Code



DMN62D1LFB

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 5) $V_{GS} = 4V$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	407	mA
		$T_A = +70^\circ\text{C}$		325	
Pulsed Drain Current (Note 6)			$I_{DM}$	1	A

**Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	$P_D$	0.5	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	251	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

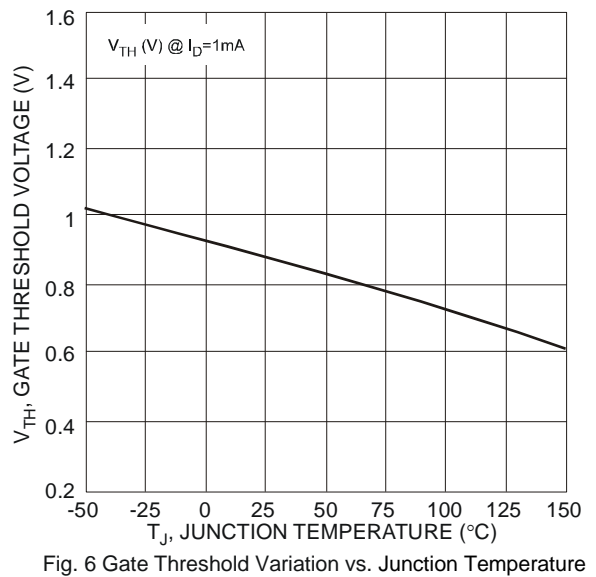
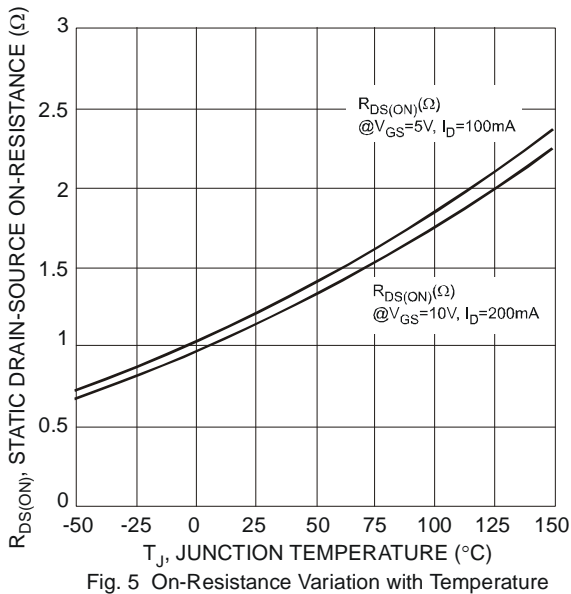
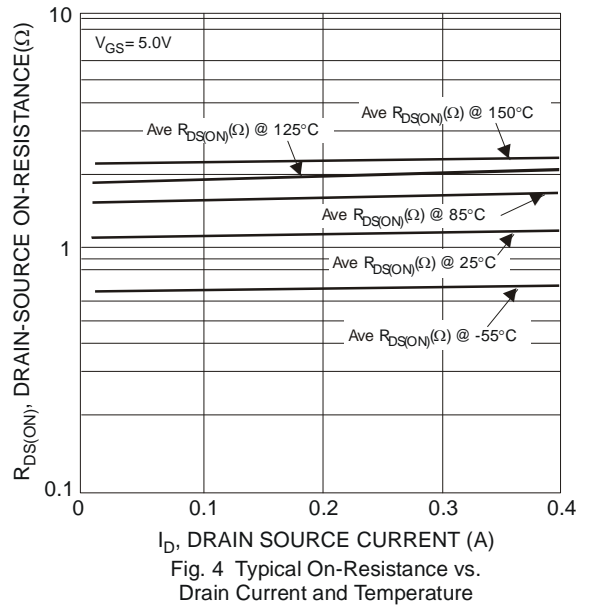
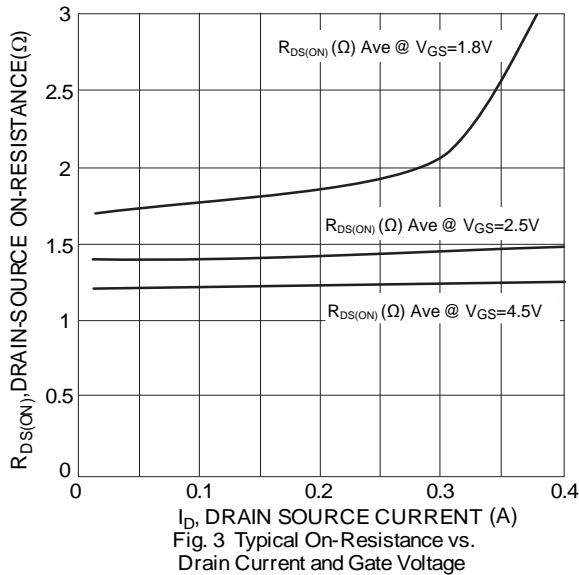
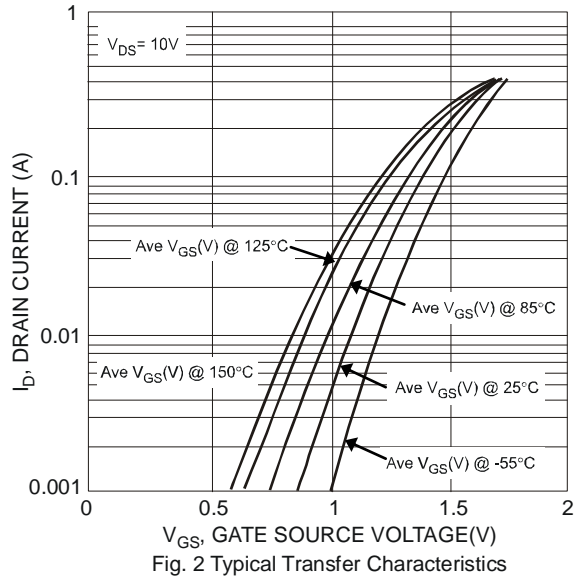
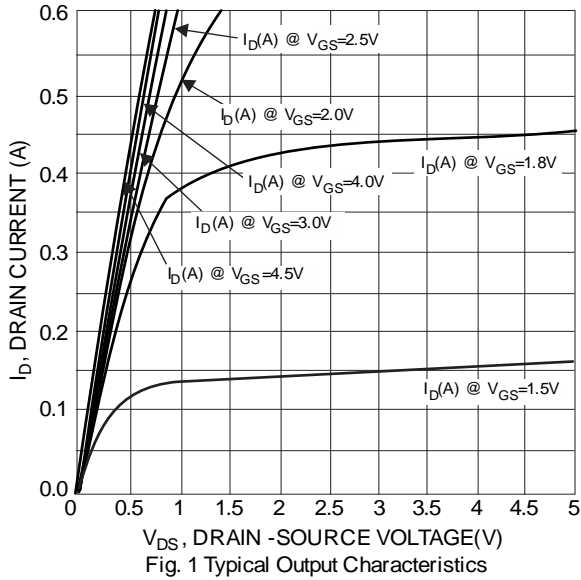
**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise stated.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	1.0	$\mu\text{A}$	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
		—	—	$\pm 500$	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
		—	—	$\pm 2.0$	$\mu\text{A}$	$V_{GS} = \pm 15V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.3	2	$\Omega$	$V_{GS} = 4V, I_D = 100\text{mA}$
		—	1.5	2.5		$V_{GS} = 2.5V, I_D = 50\text{mA}$
		—	1.9	3		$V_{GS} = 1.8V, I_D = 50\text{mA}$
Diode Forward Voltage	$V_{SD}$	—	0.9	1.3	V	$V_{GS} = 0V, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	32	64	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	4.4	9		
Reverse Transfer Capacitance	$C_{rss}$	—	2.9	6		
Gate Resistance	$R_g$	—	126	250	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge	$Q_g$	—	0.45	0.9	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250\text{mA}$
Gate-Source Charge	$Q_{gs}$	—	0.08	0.2		
Gate-Drain Charge	$Q_{gd}$	—	0.08	0.2		
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	10	ns	$V_{GS} = 10V, V_{DS} = 30V, R_L = 150\Omega, R_G = 25\Omega, I_D = 200\text{mA}$
Turn-On Rise Time	$t_R$	—	3.4	10	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.4	45	ns	
Turn-Off Fall Time	$t_F$	—	16.3	30	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.



**DMN62D1LFB**





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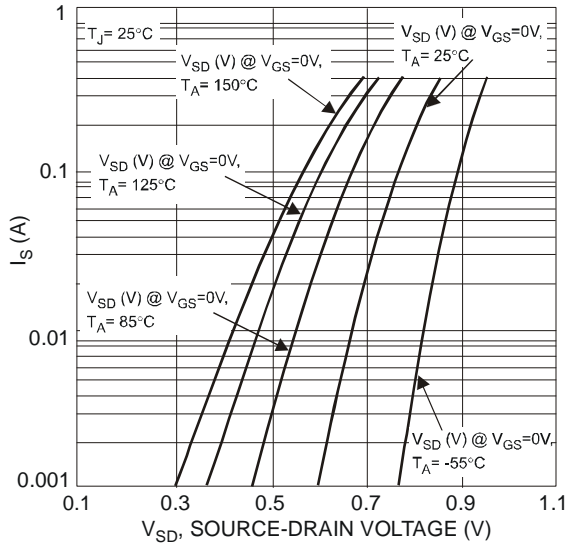


Fig. 7 Diodes Forward Voltage vs. Current

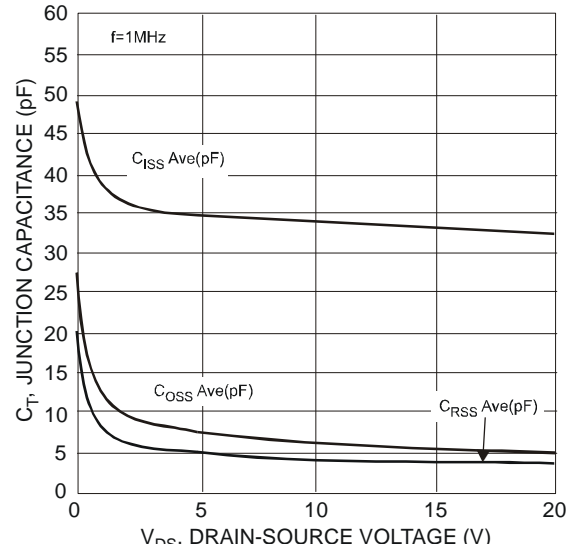


Fig. 8 Typical Junction Capacitance

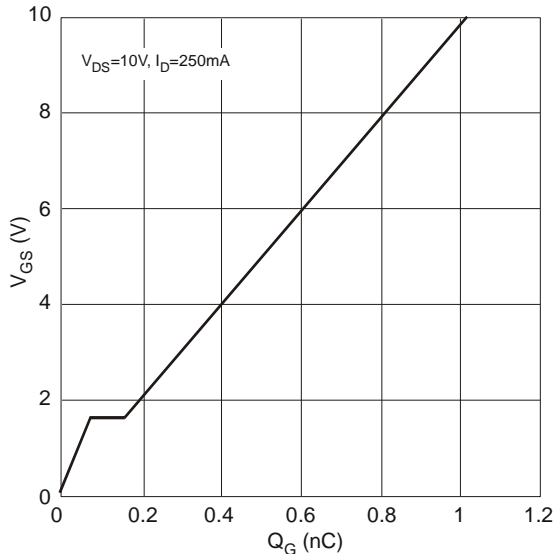


Fig. 9 Gate Charge Characteristics

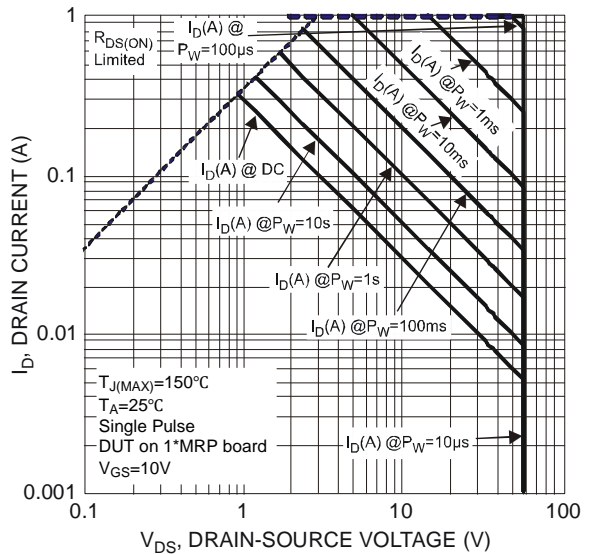


Fig. 10 SOA, Safe Operation Area

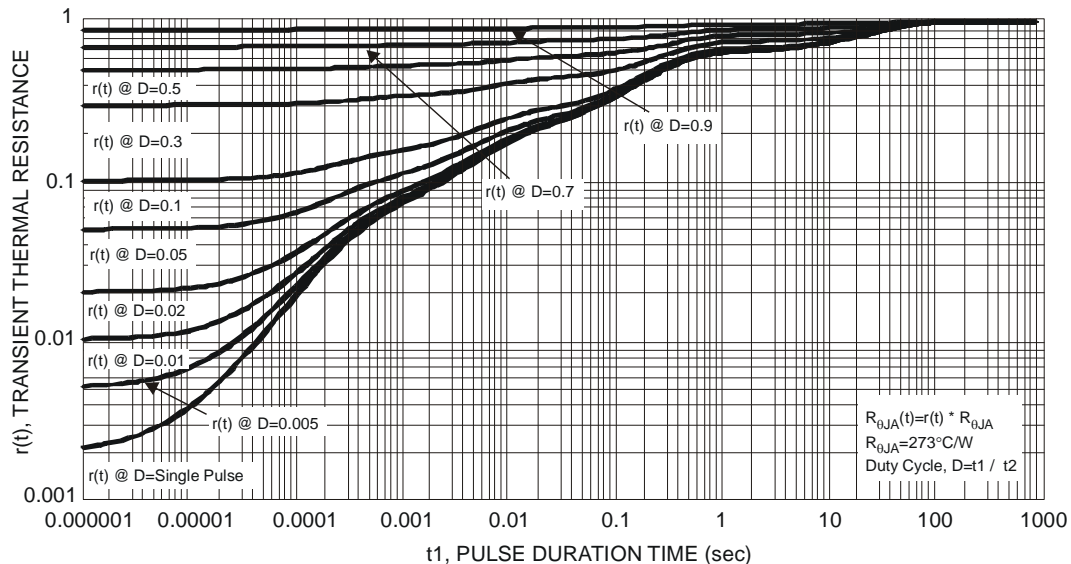
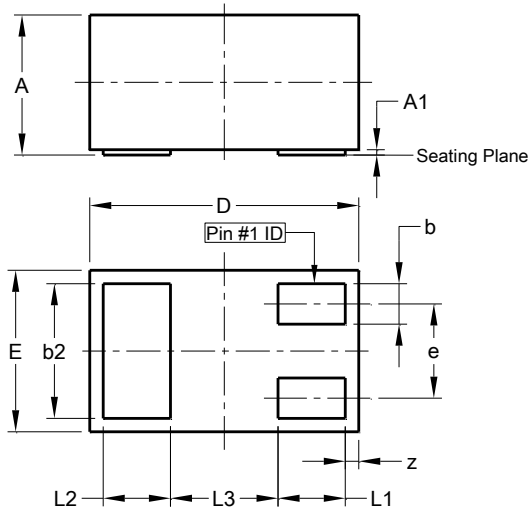


Fig. 11 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X1-DFN1006-3

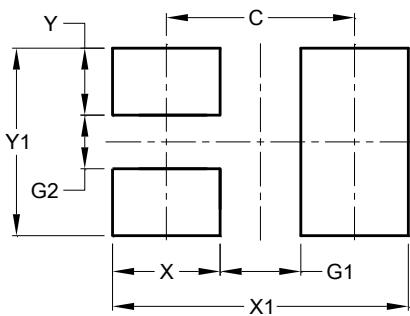


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X1-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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